

## **Influence of Boron Doping and Thermal Treatment on Internal Friction of Monocrystalline $\text{Si}_{1-x}\text{Ge}_x$ ( $x \leq 0,02$ ) Alloys**

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**Abstract :** The impact of boron doping on the internal friction (IF) and shear modulus temperature spectra of  $\text{Si}_{1-x}\text{Ge}_x$  ( $x \leq 0,02$ ) monocrystals has been investigated by reverse torsional pendulum oscillations characteristics testing. At room temperatures, microhardness and indentation modulus of the same specimens have been measured by dynamic ultra microhardness tester. It is shown that boron doping causes two kinds effect: At low boron concentration ( $\sim 10^{15} \text{ cm}^{-3}$ ) significant strengthening is revealed, while at the high boron concentration ( $\sim 10^{19} \text{ cm}^{-3}$ ) strengthening effect and activation characteristics of relaxation origin IF processes are reduced.

**Keywords :** boron, doping, internal friction, si-ge alloys, thermal treatment

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